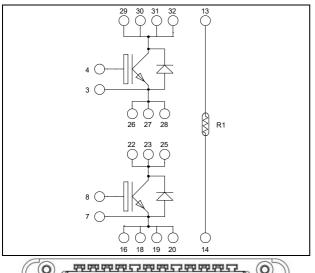
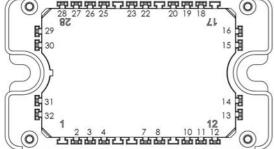


Phase leg Trench + Field Stop IGBT3 **Power Module**





Pins 29/30/31/32 must be shorted together Pins 26/27/28/22/23/25 must be shorted together to achieve a phase leg Pins 16/18/19/20 must be shorted together

APTGT150A60T3AG

$V_{CES} = 600V$ $I_C = 150A$ (*a*) $T_C = 100^{\circ}C$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

Trench + Field Stop IGBT3

- Low voltage drop
- Low tail current
- Switching frequency up to 20 kHz
- Low leakage current
- RBSOA and SCSOA rated -
- Very low stray inductance
- Kelvin emitter for easy drive
- Internal thermistor for temperature monitoring
- AlN substrate for improved thermal performance

Benefits

- Direct mounting to heatsink (isolated package) •
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive T_C of V_{CEsat}
- **RoHS** Compliant

All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (Per IGBT)

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Voltage		600	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	225	
Ic	Continuous Collector Current	$T_{\rm C} = 100^{\circ}{\rm C}$	150	Α
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	300	
V_{GE}	Gate – Emitter Voltage		±20	V
PD	Power Dissipation	$T_C = 25^{\circ}C$	600	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	300A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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Electrical Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V
V CE(sat)		$I_C = 150A$	$T_j = 150^{\circ}C$		1.7		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1.5 \text{ mA}$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			9200		
Coes	Output Capacitance	$V_{CE} = 25V$			580		pF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz			270		
Q_{G}	Gate charge	$V_{GE} = \pm 15V$; $V_{CE} = 300V$ $I_C = 150A$			1.6		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			115		
Tr	Rise Time	$V_{GE} = \pm 15V$			45		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 300V$ $I_C = 150A$			225		
$T_{\rm f}$	Fall Time	$R_G = 3.3\Omega$			55		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 150A$ $R_G = 3.3\Omega$			130		ns
Tr	Rise Time				50		
T _{d(off)}	Turn-off Delay Time				300		
T _f	Fall Time				70		
Б		$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		0.85		
Eon	Turn on Energy	$V_{Bus} = 300V$	$T_j = 150^{\circ}C$		1.5		mJ
Б		$I_{\rm C} = 150 {\rm A}$	$T_j = 25^{\circ}C$		4.1		т
E_{off}	Turn off Energy	$R_G = 3.3\Omega \qquad T_j = 150^{\circ}C$			5.3		mJ
I _{sc}	Short Circuit data				750		А
R_{thJC}	Junction to Case Thermal Resistance					0.25	°C/W

Reverse diode ratings and characteristics (Per diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage					600	V
I _{RM}	Reverse Leakage Current	$V_R = 600V$				150	μA
I_F	DC Forward Current		$Tc = 100^{\circ}C$		150		Α
V	Diada Famuand Valtaga	$I_F = 150A$	$T_j = 25^{\circ}C$		1.6	2	V
V_{F}	Diode Forward Voltage	$V_{GE} = 0V$	$T_{j} = 150^{\circ}C$		1.5		v
			$T_j = 25^{\circ}C$		100		
t_{rr}	Reverse Recovery Time		$T_j = 150^{\circ}C$		150		ns
0		$I_F = 150A$	$T_j = 25^{\circ}C$		7.2		0
Q _{rr}	Reverse Recovery Charge	$V_R = 300V$ di/dt = 2800A/µs	$T_{i} = 150^{\circ}C$		15.2		μC
Б	Deserve Deserve English	$T_i = 25^{\circ}$	$T_j = 25^{\circ}C$		1.7		
Er	Reverse Recovery Energy		$T_j = 150^{\circ}C$		3.6		mJ
R_{thJC}	Junction to Case Thermal Resistanc	e				0.42	°C/W

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Thermal and package characteristics

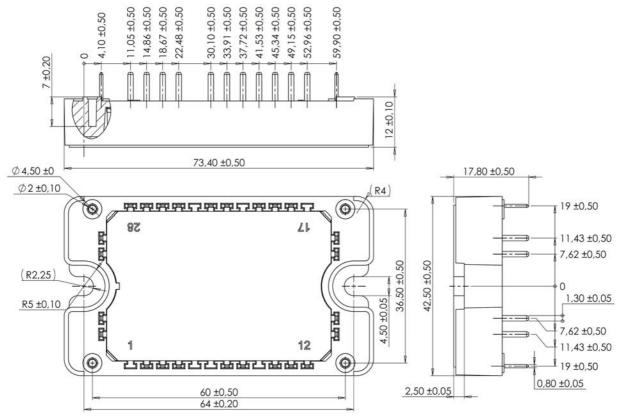
Symbol	Characteristic			Min	Max	Unit	
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V	
TJ	Operating junction temperature range			-40	175		
T _{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C	
T _{STG}	Storage Temperature Range			-40	125	C	
T _C	Operating Case Temperature				125		
Torque	Mounting torque	To heatsink	M4	2	3	N.m	
Wt	Package Weight				110	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		$T_C=100^{\circ}C$		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

Package outline (dimensions in mm)



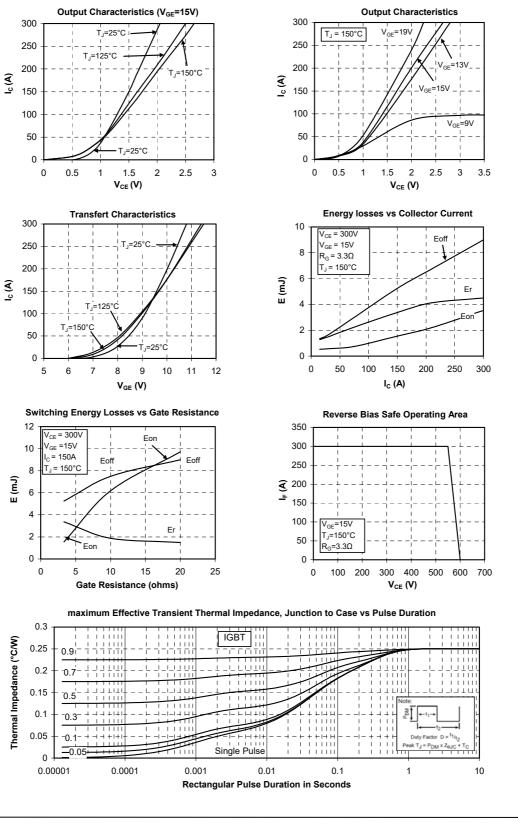
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

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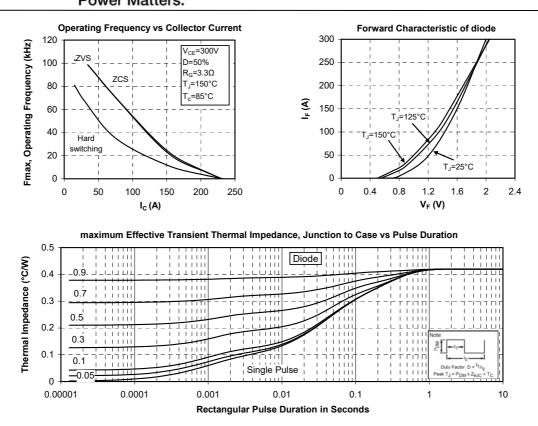
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Typical Performance Curve



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